

	Hits	Search Text	DBs
38	2	((photoreact\$4 or photocur\$5 or photosensitive or photoactiv\$5 or (light near6 sensit\$6)) same (siloxane or silicon or inorganic) same salt) and ((photoreactive or photosensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (pattern or void or interstitial or (line near9 space) or grat\$4 or vias)) and ((grat\$4 or waveguide) same (deposit\$4 or coat\$4 or form\$4 or film\$4) same (germanium or selenium or GaAs or (gallium near6 arsenide) or InP or (indium near6 phosphide) or GaInP or GaInAs or semiconductor or silicon or Si))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
39	56	((photoreactive or photoresist) same (expos\$4 or irradiat\$4 or illuminat\$4) same (pattern or void or interstitial or (line near9 space) or grat\$4 or vias)) and (pattern near26 (grat\$4 or waveguide) near16 (deposit\$4 or coat\$4 or fill\$4) near22 (germanium or selenium or GaAs or (gallium near6 arsenide) or InP or (indium near6 phosphide) or GaInP or GaInAs or semiconductor or silicon or Si))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
40	129	(((((photoreactive or photoresist) same (expos\$4 or irradiat\$4 or illuminat\$4)) or (photolithography or lithograph\$5)) same (pattern or void or intersitial or (line near9 space) or grat\$4 or vias)) and ((pattern or void) near26 (grat\$4 or waveguide) near16 (deposit\$4 or coat\$4 or fill\$4) near22 (germanium or selenium or GaAs or (gallium near6 arsenide) or InP or (indium near6 phosphide) or GaInP or GaInAs or semiconductor or silicon or Si))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
41	73	S40 Not S39	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB